

SHANGHAI SUNRISE ELECTRONICS CO., LTD.

US2AA THRU US2MA

SURFACE MOUNT ULTRA FAST SWITCHING RECTIFIER

TECHNICAL SPECIFICATION

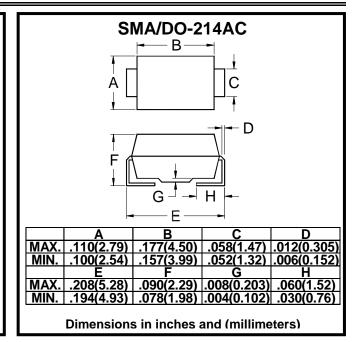
VOLTAGE: 50 TO 1000V CURRENT: 2.0A

FEATURES

- Ideal for surface mount pick and place application
- Low profile package
- Built-in strain relief
- High surge capability
- Glass passivated chip
- Ultra fast recovery for high efficiency
- High temperature soldering guaranteed: 260°C/10sec/at terminal

MECHANICAL DATA

- Terminal: Plated leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	US2 AA	US2 BA	US2 DA	US2 GA	US2 JA	US2 KA	US2 MA	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current $(T_L=90^{\circ}C)$	I _{F(AV)}	2.0						Α	
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I _{FSM}	50						А	
Maximum Instantaneous Forward Voltage (at rated forward current)	V_{F}	1.0 1.4					1.7		V
Maximum DC Reverse Current $T_a=25^{\circ}$ C (at rated DC blocking voltage) $T_a=100^{\circ}$ C		5.0 350						μ Α μ Α	
Maximum Reverse Recovery Time (Note 1)	trr	50			75			nS	
Typical Junction Capacitance (Note 2)	C_J	25						pF	
Typical Thermal Resistance (Note 3)	R _θ (ja)	20						°C/W	
Storage and Operation Junction Temperature	T_{STG},T_{J}	-50 to +150							°C

Note:

- 1.Reverse recovery condition I_F=0.5A, I_R=1.0A,Irr=0.25A.
- 2.Measured at 1.0 MHz and applied voltage of 4.0V_{dc}
- 3. Thermal resistance from junction to terminal mounted on 5×5mm copper pad area

http://www.sse-diode.com